

Received Event (Event Succeeded)

Date: 8/30/99
Pages: 5
Sender: 2079382323

Time: 3:55 PM
Duration: 1 min 12 sec
Fax Number:

In the Claims:

C1

1 1. (twice amended) A method of preparing a carbon-doped group
2 III-V compound semiconductor crystal, comprising the steps of:
3 placing a compound raw material, solid carbon, and a boron
4 oxide substance into a crucible or a boat,
5 sealing said crucible or boat containing said compound raw
6 material, said solid carbon, and said boron oxide substance
7 within an airtight vessel formed of a gas impermeable material,
8 heating and melting said compound raw material in said
9 crucible or said boat sealed within said airtight vessel, and
10 solidifying said melted compound raw material to grow a
11 carbon-doped compound semiconductor crystal. [.]
12 wherein an amount of said solid carbon placed into said
13 crucible or said boat is larger than an amount of carbon doped
14 into said compound semiconductor crystal.

Claims 2 to 5 remain as previously amended.

Please cancel claim 6.

Claim 7,

line 2, after "claim", replace "6", by --1--.

Claims 8 to 20 remain as previously amended.

Claim 21 is maintained unchanged.

3442/WFF:nr

- 2 -